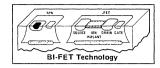


Operational Amplifiers/Buffers

LF155/LF156/LF157 Series Monolithic JFET Input Operational Amplifiers



LF155, LF155A, LF255, LF355A, LF355B, low supply current LF156, LF156A, LF256, LF356A, LF356B, wide band LF157, LF157A, LF257, LF357A, LF357B, wide band decompensated (AV_{MIN} = 5)

General Description

These are the first monolithic JFET input operational amplifiers to incorporate well matched, high voltage JFETs on the same chip with standard bipolar transistors (BI-FET Technology). These amplifiers feature low input bias and offset currents, low offset voltage and offset voltage and offset voltage drift, coupled with offset adjust which does not degrade drift or common-mode rejection. The devices are also designed for high slew rate, wide bandwidth, extremely fast settling time, low voltage and current noise and a low 1/f noise corner.

Advantages

- Replace expensive hybrid and module FET op amps
- Rugged JFETs allow blow-out free handling compared with MOSFET input devices
- Excellent for low noise applications using either high or low source impedance—very low 1/f corner
- Offset adjust does not degrade drift or common-mode rejection as in most monolithic amplifiers
- New output stage allows use of large capacitive loads (10,000 pF) without stability problems
- Internal compensation and large differential input voltage capability

Applications

- Precision high speed integrators
- Fast D/A and A/D converters
- High impedance buffers
- Wideband, low noise, low drift amplifiers
- Logarithmic amplifiers

- Photocell amplifiers
- Sample and Hold circuits

Common Features

(LF155A, LF156A, LF157A)

 Low input bias current 	30 pA
 Low Input Offset Current 	3 pA
 High input impedance 	$10^{12}\Omega$
Low input offset voltage	1 mV
Low input offset voltage temperature drift	3μV/°C
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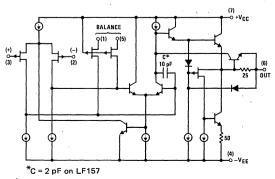
■ Low input noise current 0.01 pA/√Hz
■ High common-mode rejection ratio 100 dB

■ Large dc voltage gain 106 dB

Uncommon Features

		LF155A	LF156A	LF157A (A _V = 5)*	UNITS
	Extremely fast settling time to 0.01%	. 4	1.5	1.5	μs
=	Fast slew				
	rate	5	12	50	V/μs
	Wide gain bandwidth	2.5	5	20	MHz
-	Low input noise voltag	20	12	12	nV/√Hz

Simplified Schematic



Absolute	Maximum Ratings	LF155A/6A/7A	LF155/6/7	LF355B/6B/7B LF255/6/7 LF355B/6B/7B	LF355A/6A/7A LF355/6/7
Supply Voltage		±22V	±22V	±22V	±18V
Power Dissipation and Thermal Resi	n (P _d at 25°C) stance (θ _j Δ) (Note 1)			•	,
T_{jMAX}			•		,
(H and J P	ackage)	150°C	150°C	115°C	115°C
(N Packag	e)			100°C	100° C
(H Package)	P _d	670 mW	670 mW	570 mW	570 mW
	$\theta_{j}A$	150°C/W	150°C/W	150°C/W	150°C/W
(J Package)	P _d	670 mW	670 mW	, 570 mW	570 mW
	θ_{jA}	140° C/W	140°C/W	140°C/W	140° C/W
(N Package)	P _d	•		500 mW	500 mW
	$\theta_{j}A$			155° C/W	155° C/W
Differential Input	Voltage	±40V	±40V	±40V	±30V
Input Voltage Ra	nge (Note 2)	±20V	±20V	±20V	±16V
Output Short Circ	cuit Duration	Continuous	Continuous	Continuous	Continuous
Storage Temperat	ure Range	-65°C to +150°C	-65°C to +150°C	-65°C to +150°C	-65°C to +150°C
Lead Temperature	e (Soldering, 10 seconds)	300°C	300°C	300°C	300°C
DO Elast.	ومالواليوا ومسأواها الموا				

DC Electrical Characteristics (Note 3)

01/44001	DADAMETED	CONDITIONS	· LF	155A/6A/	7A	LF	355A/6A/	7A	LINUTO
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	UNITS
Vos	Input Offset Voltage	$R_S = 50\Omega$, $T_A = 25^{\circ}C$ Over Temperature		1	2 2.5		1	2 2.3	mV mV
$\Delta V_{OS}/\Delta T$	Average TC of Input Offset Voltage	R _S = 50Ω	i	3	5		3	5	μV/°C
ΔTC/ΔV _{OS}	Change in Average TC with VOS Adjust	$R_S = 50\Omega$, (Note 4)		0.5			0.5		μV/°C per mV
los	Input Offset Current	$T_j = 25^{\circ}C$, (Notes 3, 5) $T_j \le T_{HIGH}$		3	10 10		3	10 1	pA nA
IB	Input Bias Current	$T_J = 25^{\circ}C$, (Notes 3, 5) $T_J \le T_{HIGH}$		30	50 25		30	50 5	pA nA
RIN	Input Resistance	T _J = 25°C	ľ	1012			1012		Ω
AVOL	Large Signal Voltage Gain	$V_S = \pm 15V$, $T_A = 25^{\circ}C$ $V_O = \pm 10V$, $R_L = 2k$	50	200		50	200		V/mV
		Over Temperature	25			25			V/mV
v ₀	Output Voltage Swing	$V_S = \pm 15V$, $R_L = 10k$ $V_S = \pm 15V$, $R_L = 2k$	±12 ±10	±13 ±12		±12 ±10	±13 ±12		\ \ \ \ \
V _{CM}	Input Common-Mode Voltage Range	V _S = ±15V	. ±11	+15,1 -12		±11	+15.1 -12		V
CMRR	Common-Mode Rejection Ratio		85	. 100		85	100		dB [*]
PSRR	Supply Voltage Rejection	(Note 6)	85	.100		85	100		dB

AC Electrical Characteristics TA = 25°C, VS = ±15V

DADAMETED	CONDITIONS	LF155A/355A									UNITS
FANAMETEN	CONDITIONS	MIN	TYP	MAX	MIN	MIN TYP MAX		MIN	TYP	MAX	ONITS
Slew Rate	LF155A/6A; Ay = 1,	3	5		10	12					V/μs
	LF157A; A _V = 5	· ·						40	50		V/μs
Gain Bandwidth		١.	2.5		4	4.5		15	20		MHz
Product	\$.										
Settling Time to 0.01%	(Note 7) ,		4		'	1.5			1,5		μs
Equivalent Input Noise	$R_S = 100\Omega$	ĺ					`		-		
Voltage	f = 100 Hz	1	25			15			15		nV/√Hz
	f = 1000 Hz	1	25			12		1	12		nV/√Hz
Equivalent Input	f = 100 Hz		0.01			0.01	İ		0.01		pA/√Hz
Noise Current	f = 1000 Hz	ļ	-0.01			0.01	l	İ	0.01		pA/√Hz
Input Capacitance		-	3			3			3		pF
	Gain Bandwidth Product Settling Time to 0.01% Equivalent Input Noise Voltage Equivalent Input Noise Current	$ \begin{array}{lll} \text{Slew Rate} & & \text{LF155A/6A; AV} = 1, \\ \text{LF157A; AV} = 5 \\ \\ \text{Gain Bandwidth} & \\ \text{Product} & \\ \text{Settling Time to 0.01\%} & \\ \text{Equivalent Input Noise} & \\ \text{Voltage} & & \text{f} = 100 \text{Mz} \\ \text{f} = 1000 \text{Hz} & \\ \text{Equivalent Input} & \\ \text{Noise Current} & & \text{f} = 1000 \text{Hz} \\ \end{array} $	PARAMETER CONDITIONS MIN Slew Rate LF155A/6A; Ay = 1, LF157A; Ay = 5 Gain Bandwidth Product (Note 7) Settling Time to 0.01% (Note 7) Equivalent Input Noise Rs = 100Ω f = 100 Hz f = 100 Hz f = 100 Hz hoise Current Fequivalent Input f = 100 Hz f = 100 Hz hoise Current	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	PARAMETER CONDITIONS MIN TYP MAX MIN Slew Rate LF155A/6A; $A_V = 1$, LF157A; $A_V = 5$ 3 5 10 Gain Bandwidth Product 2.5 4 Settling Time to 0.01% (Note 7) 4 Equivalent Input Noise RS = 100Ω 25 Voltage f = 100 Hz 25 Equivalent Input f = 100 Hz 0.01 Noise Current f = 1000 Hz 0.01	PARAMETER CONDITIONS MIN TYP MAX MIN TYP Slew Rate LF155A/6A; A _V = 1, LF157A; A _V = 5 3 5 10 12 Gain Bandwidth Product 2.5 4 4.5 Settling Time to 0.01% Equivalent Input Noise (Note 7) 4 1.5 Equivalent Input Noise F = 100 Hz F 100 Hz 25 15 Fequivalent Input F 100 Hz 0.01 0.01 Noise Current f = 1000 Hz 0.01 0.01	PARAMETER CONDITIONS MIN TYP MAX MIN TYP MAX Slew Rate LF155A/6A; Ay = 1, LF157A; Ay = 5 3 5 10 12 12 Gain Bandwidth Product 2.5 4 4.5 4 4.5 4 Settling Time to 0.01% (Note 7) 4 1.5 4 1.5 4 1.5 4 1.5	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	PARAMETER CONDITIONS MIN TYP MAX MIS 40 50 15

DC Electrical Characteristics (Note 3)

SYMBOL	PARAMETER	CONDITIONS		LF155/6/7			F255/6/ 355B/6B		'i	_F355/6/	7	UNITS
			MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
Vos	Input Offset Voltage	$R_S = 50\Omega$, $T_A = 25^{\circ}C$ Over Temperature		3	5 7		3	5 6.5		3	10 13	mV mV
ΔV _{OS} /ΔΤ	Average TC of Input Offset Voltage	R _S = 50Ω		5			5			5		μV/°C
ΔTC/ΔV _{OS}	Change in Average TC with VOS Adjust	$R_S = 50\Omega$, (Note 4)		0.5			0.5	,		0.5		μV/°C per mV
los	Input Offset Current	$T_j = 25^{\circ}C$, (Notes 3, 5) $T_j \le T_{HIGH}$		3	20 20		3	20 1		3	50 2	pA nA
IB	Input Bias Current	$T_J = 25^{\circ}C$, (Notes 3, 5) $T_J \le T_{HIGH}$		30	100 50		30,	100 5		30	200 8	pA nA
RIN	Input Resistance	T _J = 25°C		1012			1012	,		1012		Ω
AVOL	Large Signal Voltage Gain	$V_S = \pm 15V, T_A = 25^{\circ}C$ $V_O = \pm 10V, R_L = 2k$	50	200		50	200		25	200		V/mV
		Over Temperature	25			25			15			V/mV
v _o	Output Voltage Swing	V _S = ±15V, R _L = 10k V _S = ±15V, R _L = 2k	±12 ±10	±13 ±12		±12 ±10	±13 ±12		±12 ±10	±13 ±12		V V
VCM	Input Common-Mode Voltage Range	V _S = ±15V	±11	+15.1 -12		±11	+15.1 -12		±10	+15.1 -12		v v
CMRR	Common-Mode Rejection Ratio	:	85	100		85	100	,	80	100		dB
PSRR	Supply Voltage Rejec- Ratio	(Note 6)	85	100		85	100		80	100		dB

DC Electrical Characteristics $T_A = 25^{\circ}C$, $V_S = \pm 15V$

PARAMETER	LF155A/155, LF255, LF355A/355B		LF:	LF355		LF156A/156, LF256/356B		LF356A/356		LF157A/157 LF257/357B		7A/357	UNITS
	TYP	MAX	TYP	MAX	TYP	MAX	TYP	MAX	TYP	MAX	TYP	MAX	
Supply Current	2	4	2	4	5	7	5	10	5	· 7	5	10	mA

AC Electrical Characteristics $T_A = 25^{\circ}C$, $V_S = \pm 15V$

SYMBOL	PARAMETER	CONDITIONS	LF155/255/ 355/355B TYP	LF156/256, LF356B MIN	LF156/256/ 356/356B TYP	LF157/257, LF357B MIN	LF157/257/ 357/357B TYP	UNITS
SR	Slew Rate	LF155/6: A _V = 1, LF157: A _V = 5	5	7.5	12	30	50	V/μs V/μs
GBW	Gain Bandwidth Product		2.5		5		20	MHz
ts	Settling Time to 0.01%	(Note 7)	4		1.5		1,5	μs
en	Equivalent Input Noise	R _S = 100Ω		` '	,			
,	Voltage	f = 100 Hz	25		15		15	nV/√Hz
	'	f = 1000 Hz	20		12		12	nV/√Hz
in	Equivalent Input	f = 100 Hz	0.01		0.01		0.01	pA/√Hz
	Current Noise	f = 1000 Hz	0.01	1	0.01	,	0.01	pA/√Hz
CIN	Input Capacitance	İ	3 -		3		3	pF

Notes for Electrical Characteristics

Note 1: The maximum power dissipation for these devices must be derated at elevated temperatures and is dictated by T_{1MAX} , θ_{1A} , and the ambient temperature, T_A . The maximum available power dissipation at any temperature is $P_d = (T_{1MAX} - T_A)/\theta_{1A}$ or the 25° C P_{dMAX} , whichever is less.

Note 2: Unless otherwise specified the absolute maximum negative input voltage is equal to the negative power supply voltage.

Note 3: Unless otherwise stated, these test conditions apply:

	LF155A/6A/7A LF155/6/7	LF255/6/7	LF355A/6A/7A	LF355B/6B/7B	LF355/6/7
Supply Voltage, V _S	$\pm 15V \le V_S \le \pm 20V$	$\pm 15V \le V_{\mbox{S}} \le \pm 20V$	$\pm 15V \le V_S \le \pm 18V$	$\pm 15V \le V_S \pm 20V$	V _S = ±15V
T_A	$-55^{\circ} \text{C} \le \text{T}_{A} \le +125^{\circ} \text{C}$	-25° C \leq T _A \leq +85 $^{\circ}$ C	0° C ≤ T _A ≤ +70° C	0°C ≤ TA ≤ +70°C,	0°C ≤ T _A ≤ +70°C
THIGH	+125°C	+85°C	+70°C	+70°C	+70° C

and VOS, IB and IOS are measured at VCM = 0.

OUTPUT SINK CURRENT (mA)

Note 4: The Temperature Coefficient of the adjusted input offset voltage changes only a small amount $(0.5\mu\text{V})^{\circ}\text{C}$ typically) for each mV of adjustment from its original unadjusted value. Common-mode rejection and open loop voltage gain are also unaffected by offset adjustment.

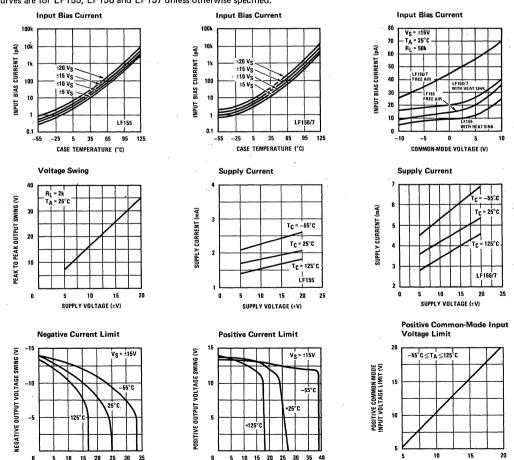
Note 5: The input bias currents are junction leakage currents which approximately double for every 10° C increase in the junction temperature, T_J . Due to limited production test time, the input bias currents measured are correlated to junction temperature. In normal operation the junction temperature rises above the ambient temperature as a result of internal power dissipation, Pd. $T_j = T_A + \Theta_{jA}$ Pd where Θ_{jA} is the thermal resistance from junction to ambient. Use of a heat sink is recommended if input bias current is to be kept to a minimum.

Note 6: Supply Voltage Rejection is measured for both supply magnitudes increasing or decreasing simultaneously, in accordance with common practice

Note 7: Settling time is defined here, for a unity gain inverter connection using 2 $k\Omega$ resistors for the LF155/6. It is the time required for the error voltage (the voltage at the inverting input pin on the amplifier) to settle to within 0.01% of its final value from the time a 10V step input is applied to the inverter. For the LF157, $A_V = -5$, the feedback resistor from output to input is 2 $k\Omega$ and the output step is 10V (See Settling Time Test Circuit, page 3-9).

Typical DC Performance Characteristics

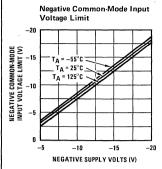
Curves are for LF155, LF156 and LF157 unless otherwise specified.

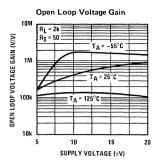


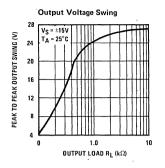
OUTPUT SOURCE CURRENT (mA)

POSITIVE SUPPLY VOLTS (V)

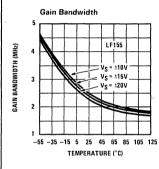
Typical DC Performance Characteristics (Continued)

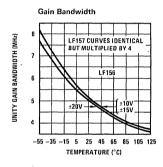


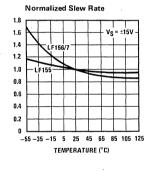


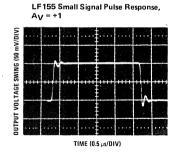


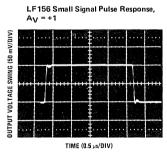
Typical AC Performance Characteristics

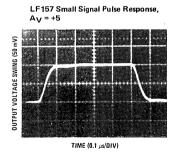




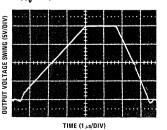


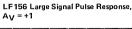


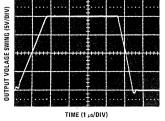




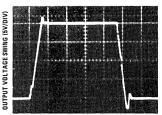




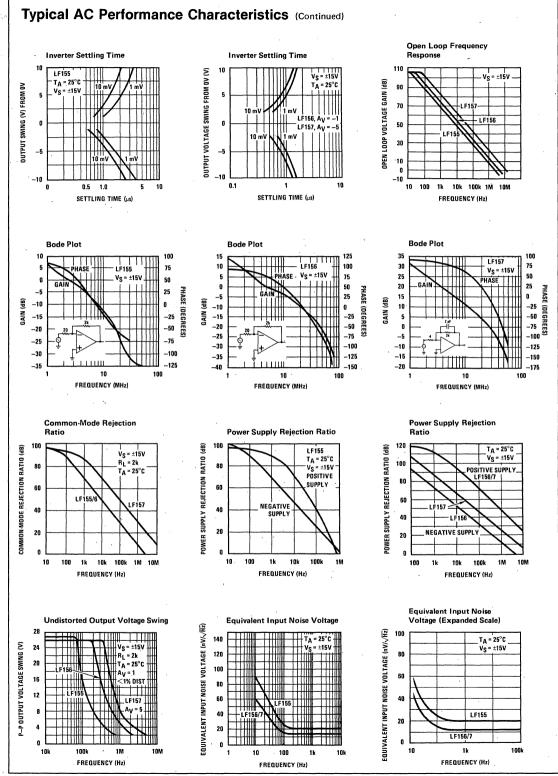




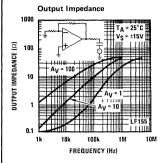
LF157 Large Signal Pulse Response, A_V = +5

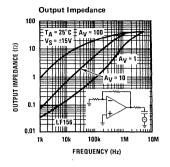


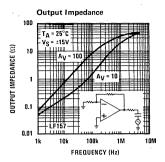
TIME (0.5 µs/DIV)



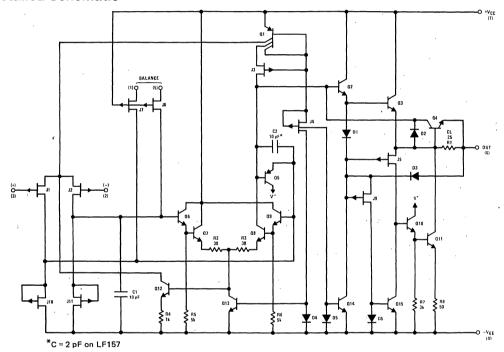
Typical AC Performance Characteristics (Continued)





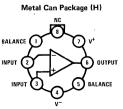


Detailed Schematic

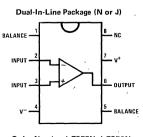


Connection Diagrams (Top Views)





Note 4: Pin 4 connected to case.



Order Number LF355N, LF356N or LF357N See NS Package N08B

Application Hints

The LF155/6/7 series are op amps with JFET input devices. These JFETs have large reverse breakdown voltages from gate to source and drain eliminating the need for clamps across the inputs. Therefore large differential input voltages can easily be accomodated without a large increase in input current. The maximum differential input voltage is independent of the supply voltages. However, neither of the input voltages should be allowed to exceed the negative supply as this will cause large currents to flow which can result in a destroyed unit.

Exceeding the negative common-mode limit on either input will cause a reversal of the phase to the output and force the amplifier output to the corresponding high or low state. Exceeding the negative common-mode limit on both inputs will force the amplifier output to a high state. In neither case does a latch occur since raising the input back within the common-mode range again puts the input stage and thus the amplifier in a normal operating mode.

Exceeding the positive common-mode limit on a single input will not change the phase of the output however, if both inputs exceed the limit, the output of the amplifier will be forced to a high state.

These amplifiers will operate with the common-mode input voltage equal to the positive supply. In fact, the common-mode voltage can exceed the positive supply by approximately 100 mV independent of supply voltage and over the full operating temperature range. The positive supply can therefore be used as a reference on an input as, for example, in a supply current monitor and/or limiter.

Precautions should be taken to ensure that the power supply for the integrated circuit never becomes reversed in polarity or that the unit is not inadvertently installed backwards in a socket as an unlimited current surge through the resulting forward diode within the IC could cause fusing of the internal conductors and result in a destroyed unit.

Because these amplifiers are JFET rather than MOSFET input op amps they do not require special handling.

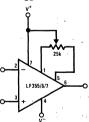
All of the bias currents in these amplifiers are set by FET current sources. The drain currents for the amplifiers are therefore essentially independent of supply voltage.

As with most amplifiers, care should be taken with lead dress, component placement and supply decoupling in order to ensure stability. For example, resistors from the output to an input should be placed with the body close to the input to minimize "pickup" and maximize the frequency of the feedback pole by minimizing the capacitance from the input to ground.

A feedback pole is created when the feedback around any amplifier is resistive. The parallel resistance and capacitance from the input of the device (usually the inverting input) to ac ground set the frequency of the pole. In many instances the frequency of this pole is much greater than the expected 3 dB frequency of the closed loop gain and consequently there is negligible effect on stability margin. However, if the feedback pole is less than approximately six times the expected 3 dB frequency a lead capacitor should be placed from the output to the input of the op amp. The value of the added capacitor should be such that the RC time constant of this capacitor and the resistance it parallels is greater than or equal to the original feedback pole time constant.

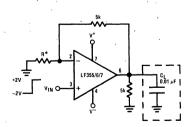
Typical Circuit Connections

VOS Adjustment



- VOS is adjusted with a 25k potentiometer
- The potentiometer wiper is connected to V+
- For potentiometers with temperature coefficient of 100 ppm/°C or less the additional drift with adjust is $\approx 0.5 \, \mu V/^{\circ} C/mV$ of adjustment
- Typical overall drift: 5 µV/ ±(0.5 μV/°C/mV of

Driving Capacitive Loads



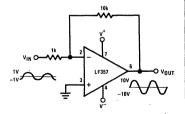
*LF155/6 R = 5k I F157 R = 1.25k

Due to a unique output stage design, these amplifiers have the ability to drive large capacitive loads and still maintain stability. $C_{L(MAX)} \approx 0.01 \mu F$.

 $Overshoot \leq 20\%$

Settling time $(t_s) \cong 5 \mu s$

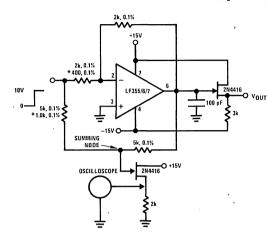
LF157. A Large Power BW Amplifier



For distortion \leq 1% and a 20 Vp-p Vour swing, power bandwidth is: 500 kHz.

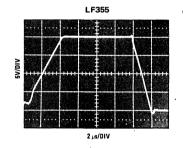
Typical Applications

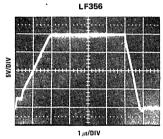
Settling Time Test Circuit

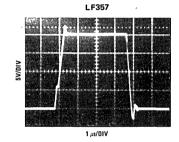


- Settling time is tested with the LF155/6 connected as unity gain inverter and LF157 connected for $A_V = -5\,$
- FET used to isolate the probe capacitance
- Output = 10V step
- $A_{V} = -5$ for LF157

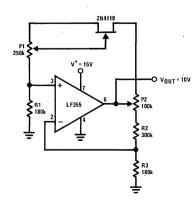
Large Signal Inverter Output, VOUT (from Settling Time Circuit)





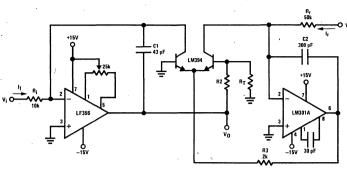


Low Drift Adjustable Voltage Reference



- $\Delta V_{OUT}/\Delta T = \pm 0.002\%/^{\circ}C$
- All resistors and potentiometers should be wire-wound
- P1: drift adjust
- P2: V_{OUT} adjust
- Use LF155 for
 - ▲ Low I_B
 - ▲ Low drift
 - ▲ Low supply current

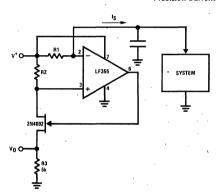
Fast Logarithmic Converter



- Dynamic range: 100 μ A \leq I_i \leq 1 mA (5 decades), |VO| = 1V/decade
- Transient response: 3 μs for ΔI; = 1 decade
- C1, C2, R2, R3: added dynamic compensation
- Vos adjust the LF156 to minimize quiescent
 error
- R_T: Tel Labs type Q81 + 0.3%/°C

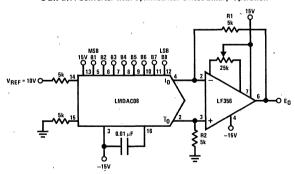
$$|V_{OUT}| = \left[1 + \frac{R2}{R_T}\right] \frac{kT}{q} \text{ In } V_i \left[\frac{R_r}{V_{REF} R_i}\right] = log \ V_i \ \frac{1}{R_i \, I_r} \quad R2 = 15.7k, \ R_T = 1k, \ 0.3\% \text{°C (for temperature compensation)}$$

Precision Current Monitor



- V_O = 5 R1/R2 (V/mA of I_S)
- R1, R2, R3: 0.1% resistors
- Use LF155 for
 - ▲ Common-mode range to supply range
 - ▲ Low In
 - ▲ Low Vos
 - ▲ Low supply current

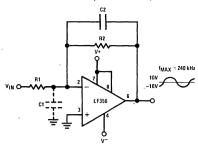
8-Bit D/A Converter with Symmetrical Offset Binary Operation



- R1, R2 should be matched within ±0.05%
- Full-scale response time: 3 μs

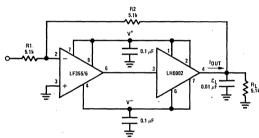
EO	В1	B2	В3	B4	B5	В6	В7	В8	COMMENTS
+9.920	1	1 .	1	1	1	1	1	1	Positive Full-Scale
+0.040	1	0	0	0	0	0	0	0	(+) Zero-Scale
-0.040	0	1	1	1	1	1	1	1	(-) Zero-Scale
-9.920	0	0	0	0	0	0	0	0	Negative Full-Scale

Wide BW Low Noise, Low Drift Amplifier



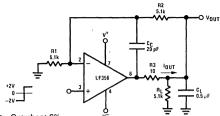
- Power BW: $f_{MAX} = \frac{S_r}{2\pi V_p} \cong 240 \text{ kHz}$

Boosting the LF156 with a Current Amplifier



- $I_{OUT(MAX)} \cong 150 \text{ mA (will drive R}_L \ge 100\Omega)$
- $\frac{\Delta V_{OUT}}{\Delta T} = \frac{0.15}{10^{-2}} V/\mu s$ (with C_L shown)
- · No additional phase shift added by the current amplifier

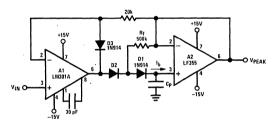
Isolating Large Capacitive Loads



- Overshoot 6%
- t_s 10 μs
- When driving large C_L, the V_{OUT} slew rate determined by C_L and I_{OUT}(MAX):

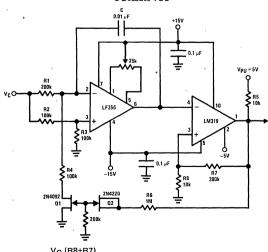
$$\frac{\Delta V_{OUT}}{\Delta T} \ = \frac{I_{OUT}}{C_L} \quad \cong \ \frac{0.02}{0.5} \quad V/\mu s = 0.04 \ V/\mu s \ (with \ C_L \ shown)$$

Low Drift Peak Detector



- By adding D1 and R_f, V_{D1} = 0 during hold mode. Leakage of D2 provided by feedback path through R_f.
- Leakage of circuit is essentially I_b (LF155, LF156) plus capacitor leakage of Cp.
- Diode D3 clamps V_{OUT} (A1) to V_{IN}-V_{D3} to improve speed and to limit reverse bias of D2.
- Maximum input frequency should be $<< 1/2\pi R_f C_{D2}$ where C_{D2} is the shunt capacitance of D2.

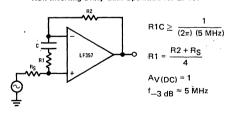
3 Decades VCO



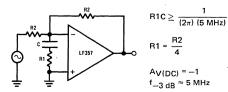
 $f = \frac{V_{C} (R8+R7)}{[8 V_{PU} R8 R1] C}, 0 \le V_{C} \le 30V, 10 Hz \le f \le 10 \text{ kHz}$

R1, R4 matched. Linearity 0.1% over 2 decades.

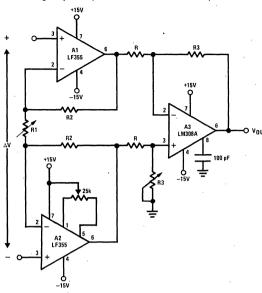
Non-Inverting Unity Gain Operation for LF157



Inverting Unity Gain for LF157

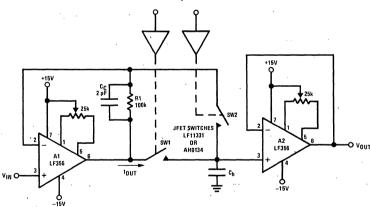


High Impedance, Low Drift Instrumentation Amplifier



- $\bullet \quad V_{OUT} = \frac{R3}{R} \left[\frac{2R2}{R1} \ + \ 1 \right] \ \Delta V, V^- + 2V \leq V_{IN} \ common-mode \leq V^+$
- System Vos adjusted via A2 Vos adjust
- Trim R3 to boost up CMRR to 120 dB. Instrumentation amplifier Resistor array RA201 (National Semiconductor) recommended

Fast Sample and Hold



- Both amplifiers (A1, A2) have feedback loops individually closed with stable responses (over-shoot negligible)
- Acquisition time T_A, estimated by:

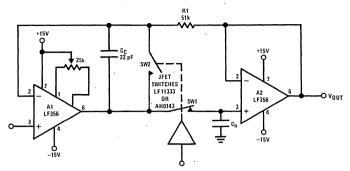
$$T_{\mbox{A}} \cong \left[\frac{2 \mbox{$R_{\mbox{$ON$}}$}, \mbox{$V_{\mbox{$IN$}}$}, \mbox{C_h}}{\mbox{S_r}} \right] \quad \mbox{$^{1/2}$ provided that:}$$

 $V_{IN} < 2\pi S_r \; R_{ON} \; C_h \; \text{and} \; T_A > \frac{V_{IN} C_h}{I_{OUT}(MAX)} \quad , \; R_{ON} \; \text{is of SW1}$

If inequality not satisfied: $T_A \cong \frac{V_{IN} C_h}{20 \text{ mA}}$

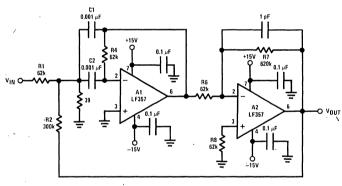
- ▶ LF156 developes full S_r output capability for $V_{IN} \ge 1V$
- Addition of SW2 improves accuracy by putting the voltage drop across SW1 inside the feedback
- . Overall accuracy of system determined by the accuracy of both amplifiers, A1 and A2

High Accuracy Sample and Hold



- By closing the loop through A2, the V_{OUT} accuracy will be determined uniquely by A1.
 No V_{OS} adjust required for A2.
- T_A can be estimated by same considerations as previously but, because of the added propagation delay in the feedback loop (A2) the overshoot is not negligible.
- Overall system slower than fast sample and hold
- R1, C_C: additional compensation
- Use LF156 for
 - ▲ Fast settling time
 - ▲ Low Vos

High Q Band Pass Filter

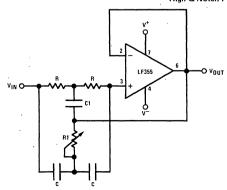


- By adding positive feedback (R2)
 Q increases to 40
- f_{BP} = 100 kHz

$$\frac{V_{OUT}}{V_{IN}} = 10\sqrt{\overline{O}}$$

- Clean layout recommended
- Response to a 1 Vp-p tone burst: 300 μs

High Q Notch Filter



- 2R1 = R = 10 MΩ 2C = C1 = 300 pF
- Capacitors should be matched to obtain high Q
- f_{NOTCH} = 120 Hz, notch = -55 dB, Q > 100
- Use LF155 for
- ▲ Low IB
- Low supply current